

Page 26, the whole paragraph starting in line 20 is changed as follows:

As shown in Figs. 5 and 6, a case purge line 15 for N2 purging the inside of the case ~~10~~ 10a is connected to the laser moisture measuring device main body 10. In addition, an N2 discharge line 16 for discharging the N2 is connected to the laser moisture measuring device main body 10. The other end of the N2 discharge line 16 connects to the process gas exhaust pipe 8.

#### IN THE ABSTRACT OF THE DISCLOSURE

The current Abstract is changed as follows:

~~Disclosed is a~~ A semiconductor manufacturing method whereby reactive gas processing such as selective epitaxial growth can be carried out with high precision by correctly adjusting conditions during processing. ~~Further disclosed are the semiconductor manufacturing method and~~ is performed by a semiconductor manufacturing apparatus which can restrict increases in the moisture content, prevent heavy metal pollution and the like, and investigate the correlation between moisture content in the process chamber and outside regions. The moisture content in a reaction chamber and in a gas discharge system of the reaction chamber are measured when a substrate is provided, and the conditions for reactive gas processing are adjusted based on the moisture content. Furthermore, the ~~method comprises a substrate carrying step of measuring the~~ moisture content in the airtight space is measured by means of a first moisture measuring device which is connected to the airtight space, and thereafter, ~~inserting and ejecting the substrate~~ is inserted and ejected by means of the a substrate carrying system, and a ~~gas processing step of performing the~~ reactive gas processing is processed while measuring the moisture content in the reaction chamber by means of a second moisture measuring device, which is connected to the reaction chamber, after the ~~substrate carrying step~~ moisture content in the airtight space is measured.